# BLF8G20LS-400PV; BLF8G20LS-400PGV

## Power LDMOS transistor

Rev. 3 — 3 June 2014 Product data sheet

## 1. Product profile

### 1.1 General description

400 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 1805 MHz to 1995 MHz.

**Table 1. Typical performance**

*Typical RF performance at $T_{case}$ = 25 °C in a common source class-AB production test circuit, tested on straight lead device.*

| Test signal | f | $I_{Dq}$ | $V_{DS}$ | $P_{L(AV)}$ | $G_p$ | $\eta_D$ | $ACPR_{5M}$ |
|---|---|---|---|---|---|---|---|
| | (MHz) | (mA) | (V) | (W) | (dB) | (%) | (dBc) |
| 2-carrier W-CDMA | 1805 to 1995 | 3400 | 28 | 95 | 19 | 28 | –33 [1] |

[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.5 dB at 0.01 % probability on CCDF; carrier spacing = 5 MHz; $f_1$ = 1807.5 MHz; $f_2$ = 1812.5 MHz; $f_3$ = 1872.5 MHz; $f_4$ = 1877.5 MHz.

### 1.2 Features and benefits

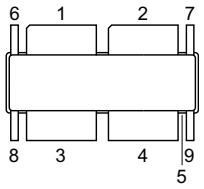
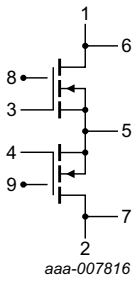
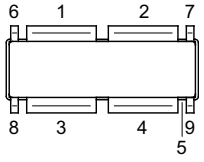
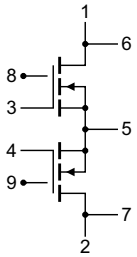
- Decoupling leads to enable improved Video BandWidth (VBW) (120 MHz typical)
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Designed for broadband operation
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Design optimized for gull-wing
- Excellent ruggedness
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- RF power amplifiers for base stations and multi carrier applications in the 1805 MHz to 1995 MHz frequency range

## 2. Pinning information

**Table 2. Pinning**

| Pin | Description | Simplified outline | Graphic symbol |
|---|---|---|---|
| **BLF8G20LS-400PV (SOT1242B)** | | | |
| 1 | drain1 |  |  |
| 2 | drain2 | | |
| 3 | gate1 | | |
| 4 | gate2 | | |
| 5 | source [1] | | |
| 6 | decoupling1 | | |
| 7 | decoupling2 | | |
| 8 | n.c. | | |
| 9 | n.c. | | |
| **BLF8G20LS-400PGV (SOT1242C)** | | | |
| 1 | drain1 |  |  |
| 2 | drain2 | | |
| 3 | gate1 | | |
| 4 | gate2 | | |
| 5 | source [1] | | |
| 6 | decoupling1 | | |
| 7 | decoupling2 | | |
| 8 | n.c. | | |
| 9 | n.c. | | |

[1] Connected to flange.

## 3. Ordering information

**Table 3. Ordering information**

| Type number | Package | | |
|---|---|---|---|
| | Name | Description | Version |
| BLF8G20LS-400PV | - | earless flanged ceramic package; 8 leads | SOT1242B |
| BLF8G20LS-400PGV | - | earless flanged ceramic package; 8 leads | SOT1242C |

# 4. Limiting values

**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|
| $V_{DS}$ | drain-source voltage | | - | 65 | V |
| $V_{GS}$ | gate-source voltage | | –0.5 | +13 | V |
| $T_{stg}$ | storage temperature | | –65 | +150 | °C |
| $T_j$ | junction temperature | [1] | - | 225 | °C |

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

# 5. Thermal characteristics

**Table 5. Thermal characteristics**

| Symbol | Parameter | Conditions | Typ | Unit |
|---|---|---|---|---|
| $R_{th(j-c)}$ | thermal resistance from junction to case | $T_{case}$ = 80 °C; $P_L$ = 80 W | 0.23 | K/W |

# 6. Characteristics

**Table 6. DC characteristics**

*$T_j$ = 25 °C; per section unless otherwise specified.*

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $V_{GS}$ = 0 V; $I_D$ = 3.0 mA | 65 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $V_{DS}$ = 10 V; $I_D$ = 300 mA | 1.5 | 1.9 | 2.3 | V |
| $I_{DSS}$ | drain leakage current | $V_{GS}$ = 0 V; $V_{DS}$ = 28 V | - | - | 3.0 | μA |
| $I_{DSX}$ | drain cut-off current | $V_{GS}$ = $V_{GS(th)}$ + 3.75 V; $V_{DS}$ = 10 V | | 51.5 | - | A |
| $I_{GSS}$ | gate leakage current | $V_{GS}$ = 11 V; $V_{DS}$ = 0 V | - | - | 300 | nA |
| $g_{fs}$ | forward transconductance | $V_{DS}$ = 10 V; $I_D$ = 15 A | - | 20.6 | - | S |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS}$ = $V_{GS(th)}$ + 3.75 V; $I_D$ = 10.5 A | - | 0.055 | - | Ω |

**Table 7. RF characteristics**

*Test signal: 2-carrier W-CDMA; PAR = 7.5 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1-64 DPCH; $f_1$ = 1807.5 MHz; $f_2$ = 1812.5 MHz; $f_3$ = 1872.5 MHz; $f_4$ = 1877.5 MHz; RF performance at $V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA; $T_{case}$ = 25 °C; unless otherwise specified; in a class-AB production test circuit, tested on straight lead device.*

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $G_p$ | power gain | $P_{L(AV)}$ = 95 W | 17.8 | 19 | - | dB |
| $RL_{in}$ | input return loss | $P_{L(AV)}$ = 95 W | - | –12 | –6 | dB |
| $\eta_D$ | drain efficiency | $P_{L(AV)}$ = 95 W | 24 | 28 | - | % |
| $ACPR_{5M}$ | adjacent channel power ratio (5 MHz) | $P_{L(AV)}$ = 95 W | - | –33 | –28 | dBc |

# 7. Test information

## 7.1 Ruggedness in class-AB operation

The BLF8G20LS-400PV and BLF8G20LS-400PGV are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS}$ = 28 V; $I_{Dq}$ = 3300 mA; 2-carrier W-CDMA signal; $P_L$ = 200 W; $f_c$ = 1800 MHz; 5 MHz spacing, 46 % clipping.

## 7.2 Impedance information

**Table 8. Typical impedance for the top-half of the push-pull package**

*Measured load-pull data; $I_{Dq}$ = 1800 mA; $V_{DS}$ = 28 V; $T_{case}$ = 25 °C, water cooled.*

| f | $Z_S$[1] | $Z_L$[1] |
|---|---|---|
| **(MHz)** | **(Ω)** | **(Ω)** |
| **BLF8G20LS-400PV (straight lead)** | | |
| 1800 | 4.1 – j4.66 | 4.1 – j4.5 |
| 1840 | 5.2 – j3.6 | 4.4 – j4.4 |
| 1880 | 4.6 – j1.45 | 4.85 – j4.25 |
| 1930 | 2.8 – j0.3 | 4.5 – j4.3 |
| 1960 | 2.1 – j0.5 | 5.5 – j3.5 |
| 1990 | 1.56 – j0.6 | 5.5 – j3.4 |
| **BLF8G20LS-400PGV (gull-wing)** | | |
| 1800 | 3.7 – j7.6 | 4.2 – j6.8 |
| 1840 | 4.34 – j6.1 | 4.4 – j6.7 |
| 1880 | 4.75 – j5.2 | 4 – j6.4 |
| 1930 | 3.17 – j3.4 | 4.6 – j6.5 |
| 1960 | 2 – j3.05 | 5.8 – j5.5 |
| 1990 | 2.5 – j2.6 | 5.8– j5.7 |

[1] $Z_S$ and $Z_L$ defined in Figure 1.

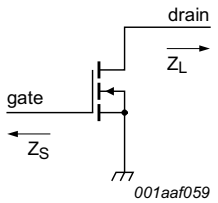
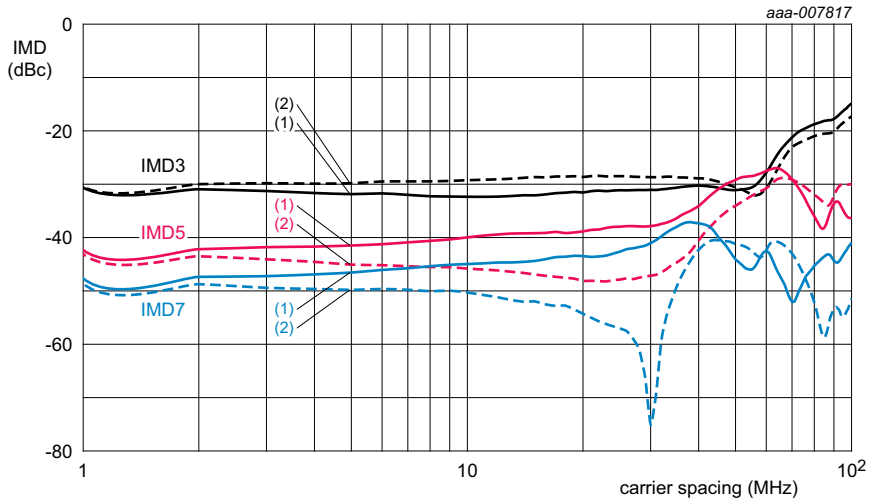



**Fig 1. Definition of transistor impedance**

## 7.3 VBW in class-AB operation

The BLF8G20LS-400PV and BLF8G20LS-400PGV have a video bandwidth of 120 MHz (typical) when measured in a class-AB test circuit operating in the 1800 MHz to 1880 MHz frequency band for $V_{DS}$ = 28 V and $I_{Dq}$ = 3.3 A, where the VBW is defined as the location of the resonance in the base-band impedance measurement obtained using a low-frequency probe.

The VBW measurement based on the 2-tone IMD test as a function of carrier spacing is shown below.

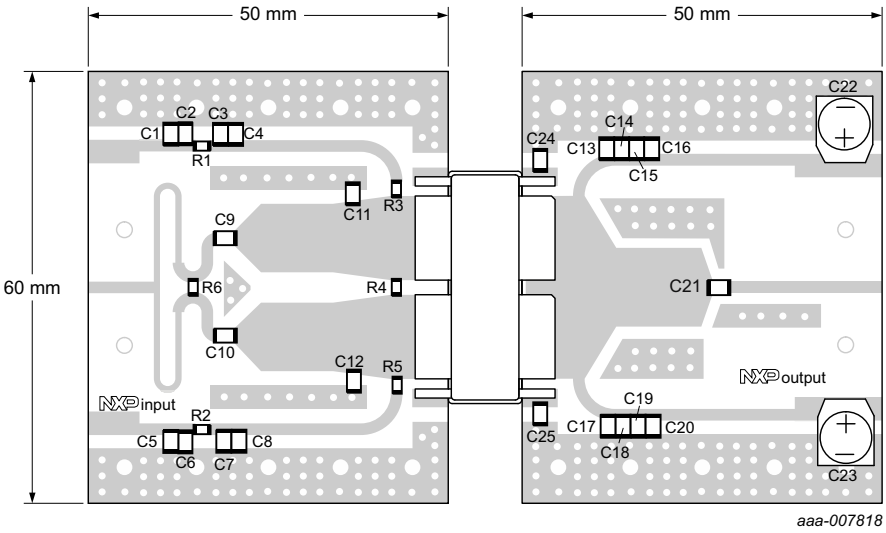



(1) IMD low

(2) IMD high

**Fig 2. VBW capacity in a class-AB test circuit**

## 7.4 Test circuit




Printed-Circuit Board (PCB): Rogers 4350B; $\varepsilon_r$ = 3.66; thickness = 0.762 mm; thickness copper plating = 35 μm.

See Table 9 for a list of components.

**Fig 3. Component layout**

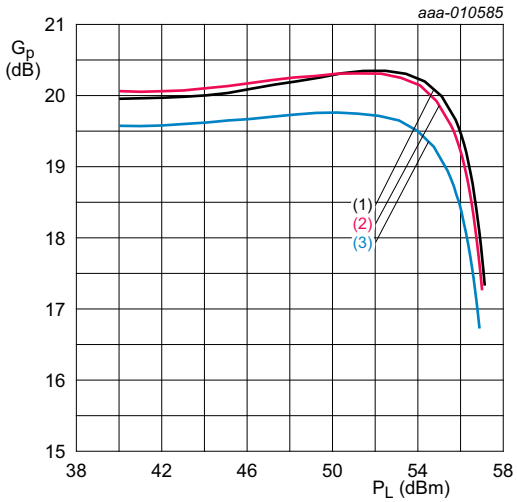
**Table 9. List of components**

*See Figure 3 for component layout.*

| Component | Description | Value | Remarks |
|---|---|---|---|
| C1, C5, C16, C20 | multilayer ceramic chip capacitor | 10 μF, 50 V | Murata, SMD 2220 |
| C2, C6, C15, C19, C24, C25 | multilayer ceramic chip capacitor | 4.7 μF, 50 V | Murata |
| C3, C7, C14, C18 | multilayer ceramic chip capacitor | 1 nF | ATC100B |
| C4, C8, C9, C10, C13, C17, C21 | multilayer ceramic chip capacitor | 24 pF | ATC100B |
| C11, C12 | multilayer ceramic chip capacitor | 100 pF | ATC100B |
| C22, C23 | electrolytic capacitor | 2200 μF, 63 V | |
| R1, R2 | resistor | 10 Ω | SMD 1206 |
| R3, R5 | resistor | 5.1 Ω | SMD 1206 |
| R4 | resistor | 33 Ω | SMD 1206 |
| R6 | resistor | 100 Ω | SMD 1206 |

## 7.5 Graphical data

### 7.5.1 Pulsed CW



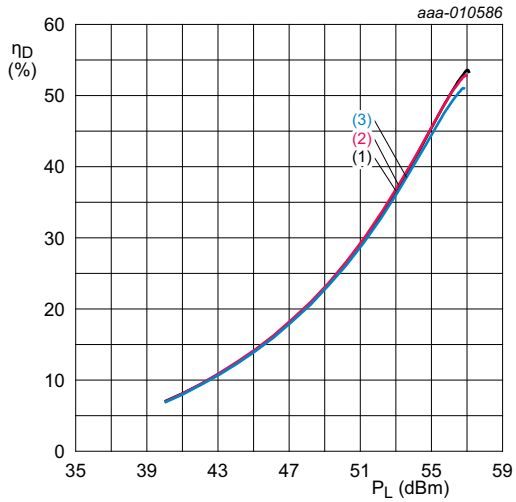

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA; $t_p$ = 100 μs; δ = 10 %.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 4. Power gain as a function of output power; typical values**




$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA; $t_p$ = 100 μs; δ = 10 %.

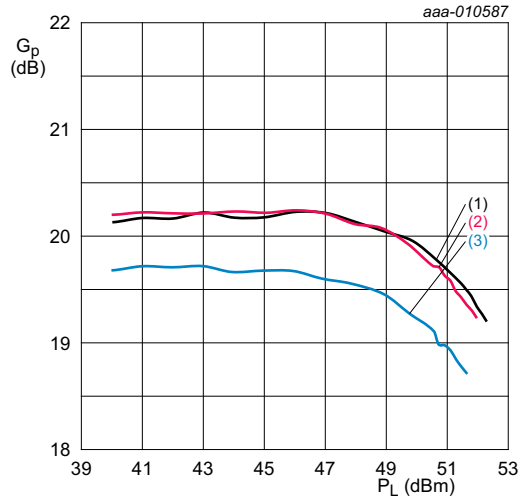
(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 5. Drain efficiency as a function of output power; typical values**

### 7.5.2 IS-95



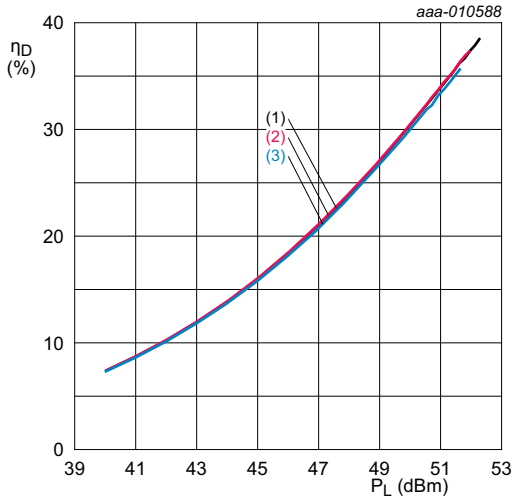

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 6. Power gain as a function of output power; typical values**



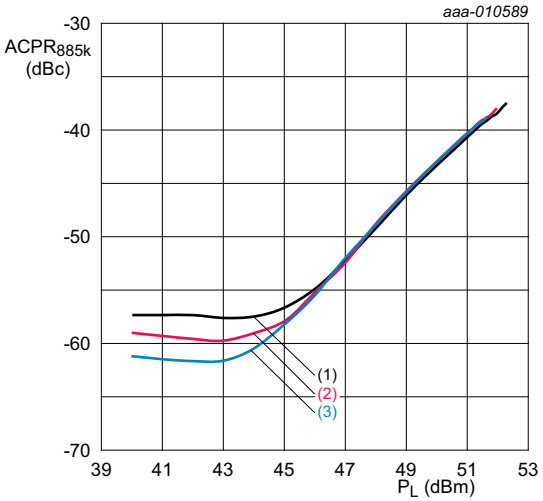

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 7. Drain efficiency as a function of output power; typical values**



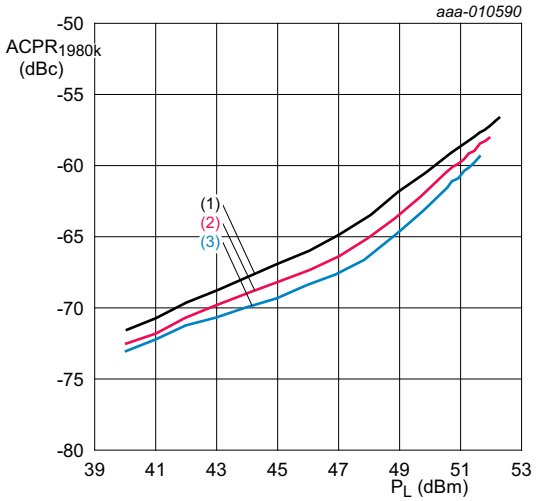

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 8. Adjacent channel power ratio (885 kHz) as a function of output power; typical values**



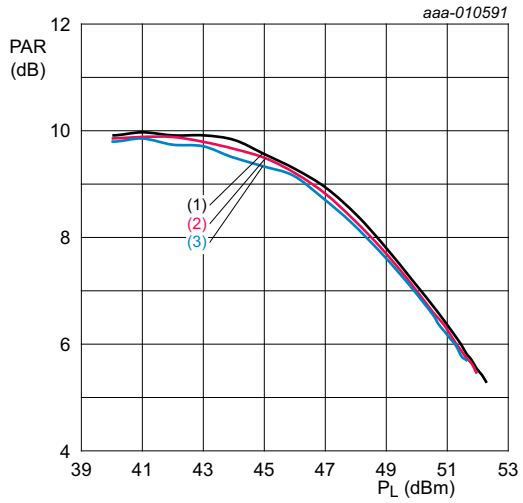

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 9. Adjacent channel power ratio (1980 kHz) as a function of output power; typical values**



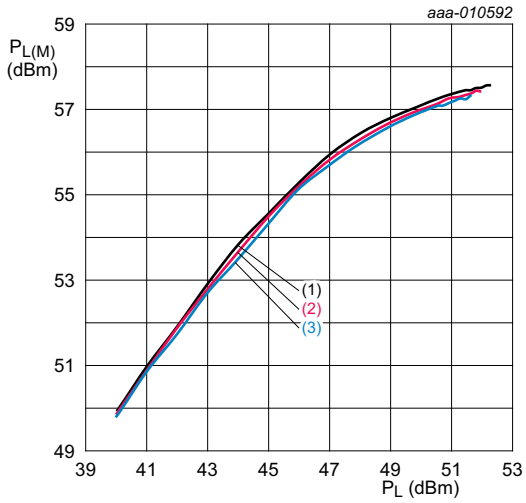

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 10. Peak-to-average ratio as a function of output power; typical values**




$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

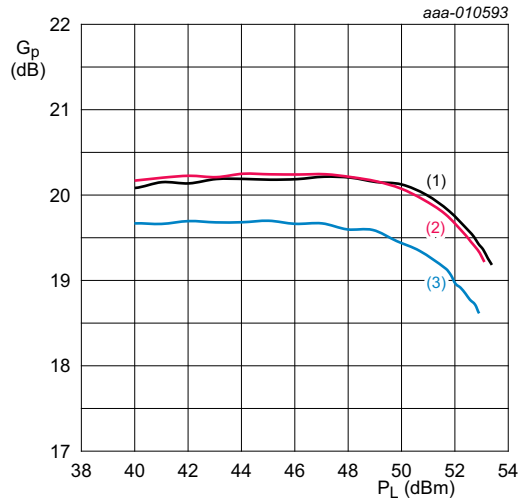
(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 11. Peak output power as a function of output power; typical values**

### 7.5.3 1-Carrier W-CDMA



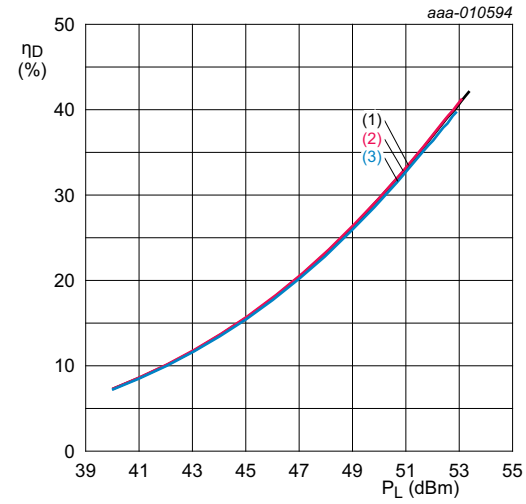

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 12. Power gain as a function of output power; typical values**



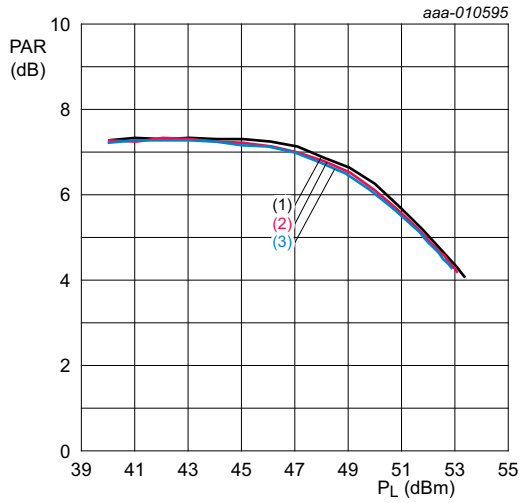

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 13. Drain efficiency as a function of output power; typical values**



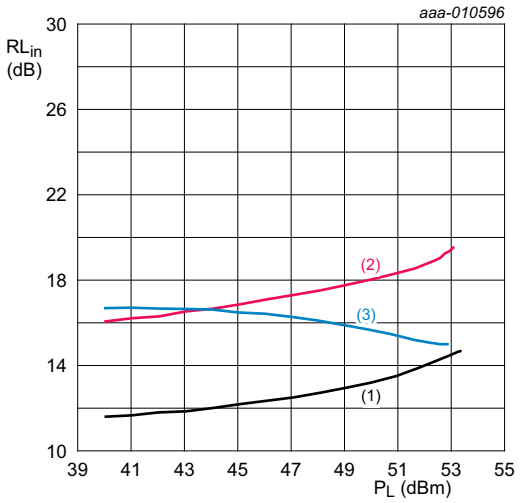

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 14. Peak-to-average ratio as a function of output power; typical values**




$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

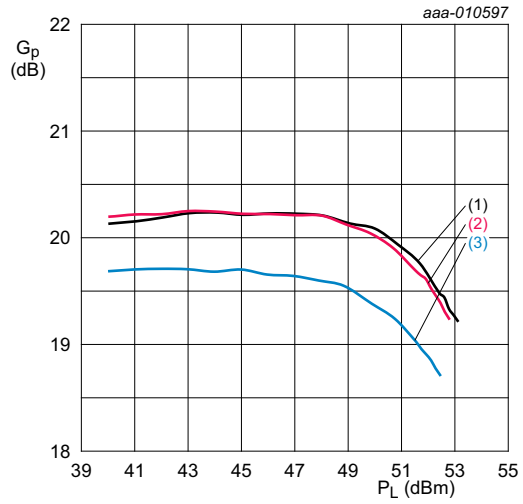
(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 15. Input return loss as a function of output power; typical values**

### 7.5.4 2-Carrier W-CDMA



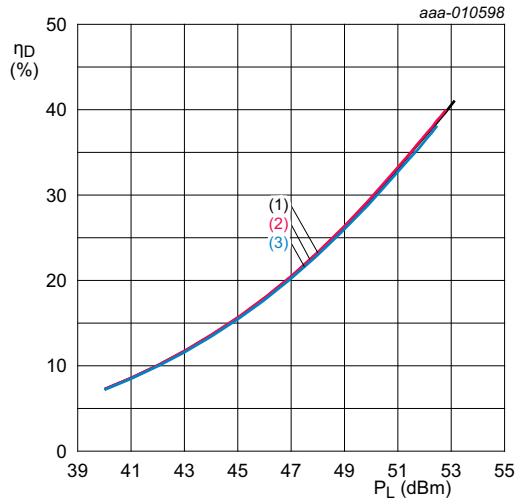

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 16. Power gain as a function of output power; typical values**



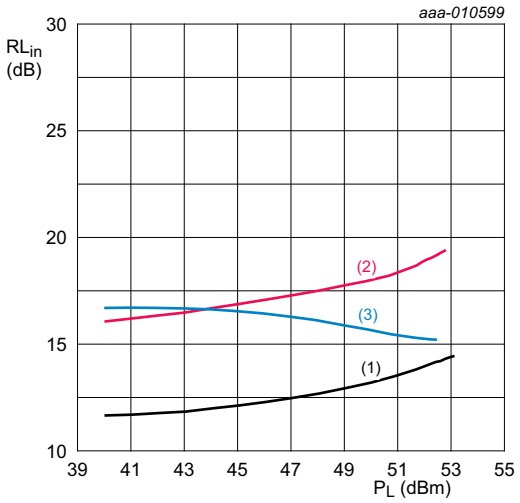

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 17. Drain efficiency as a function of output power; typical values**



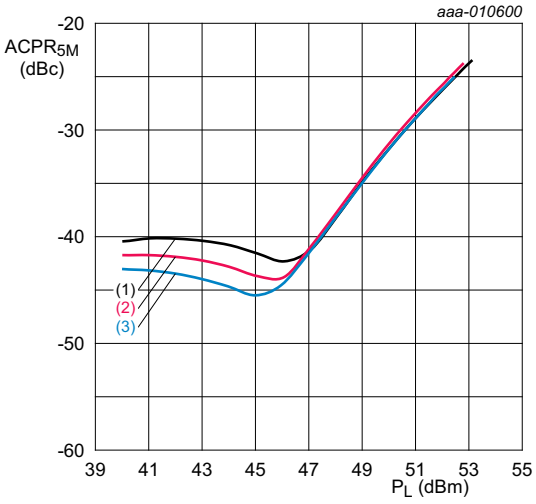

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 18. Input return loss as a function of output power; typical values**



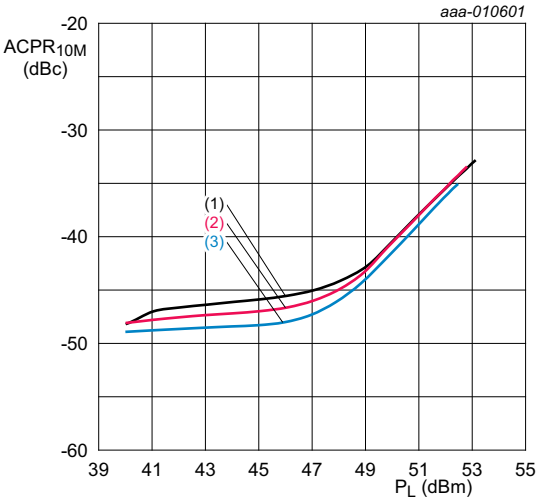

$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 19. Adjacent channel power ratio (5 MHz) as a function of output power; typical values**




$V_{DS}$ = 28 V; $I_{Dq}$ = 3400 mA.

(1) f = 1805 MHz

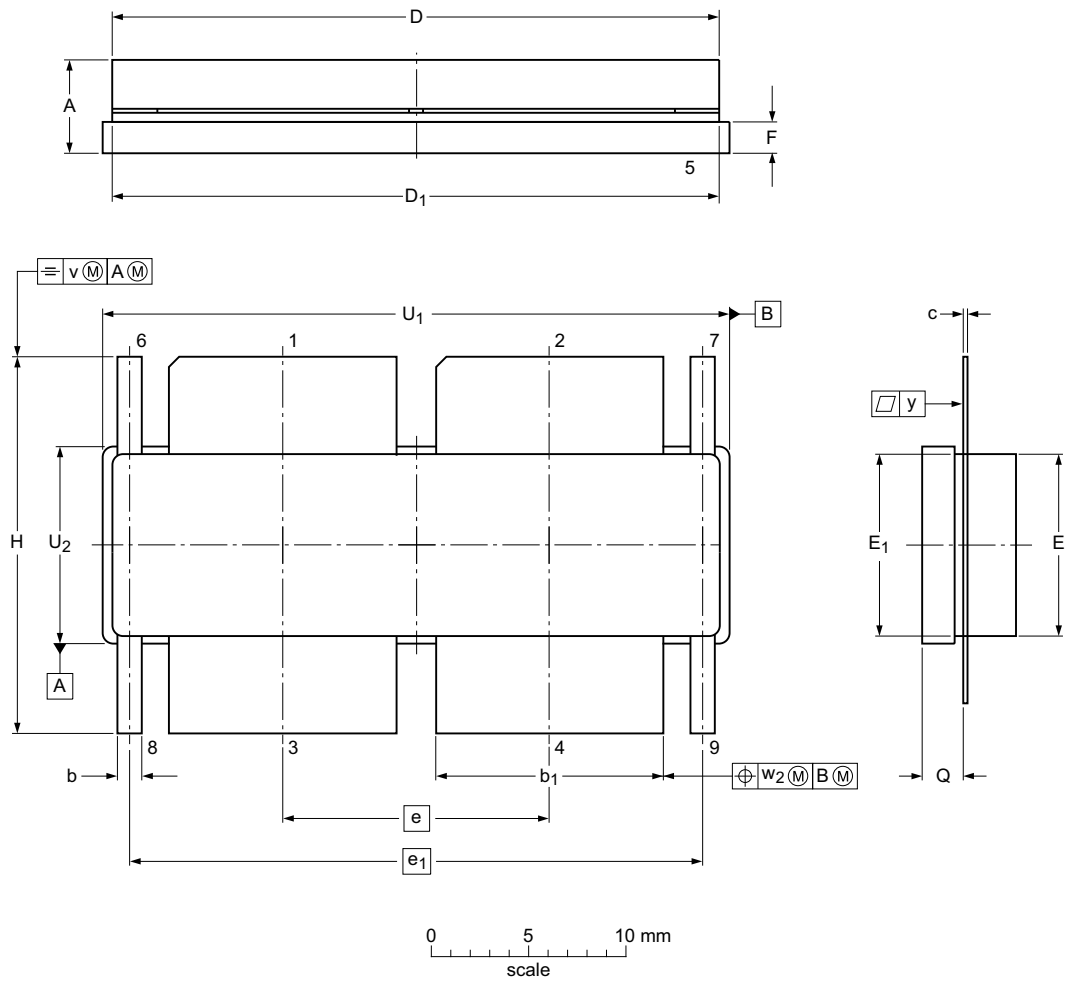
(2) f = 1840 MHz

(3) f = 1880 MHz

**Fig 20. Adjacent channel power ratio (10 MHz) as a function of output power; typical values**

# 8. Package outline

**Earless flanged ceramic package; 8 leads** **SOT1242B**




Dimensions

| Unit[1] | | A | b | $b_1$ | c | D | $D_1$ | e | $e_1$ | E | $E_1$ | F | H | Q[2] | $U_1$ | $U_2$ | v | $w_2$ | y |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| mm | max | 5.5 | 1.41 | 11.81 | 0.18 | 31.55 | 31.52 | | | 9.50 | 9.53 | 1.75 | 19.94 | 2.26 | 32.39 | 10.29 | 0.25 | 0.25 | 0.25 |
| | nom | | | | | | | 13.72 | 29.47 | | | | | | | | | | |
| | min | 4.2 | 1.14 | 11.56 | 0.10 | 30.94 | 30.96 | | | 9.30 | 9.27 | 1.50 | 18.92 | 2.01 | 32.13 | 10.03 | | | |
| inches | max | 0.217 | 0.055 | 0.465 | 0.007 | 1.242 | 1.241 | | | 0.374 | 0.375 | 0.069 | 0.785 | 0.089 | 1.275 | 0.405 | 0.010 | 0.010 | 0.010 |
| | nom | | | | | | | 0.540 | 1.16 | | | | | | | | | | |
| | min | 0.165 | 0.045 | 0.455 | 0.004 | 0.218 | 1.219 | | | 0.366 | 0.365 | 0.059 | 0.745 | 0.079 | 1.265 | 0.395 | | | |

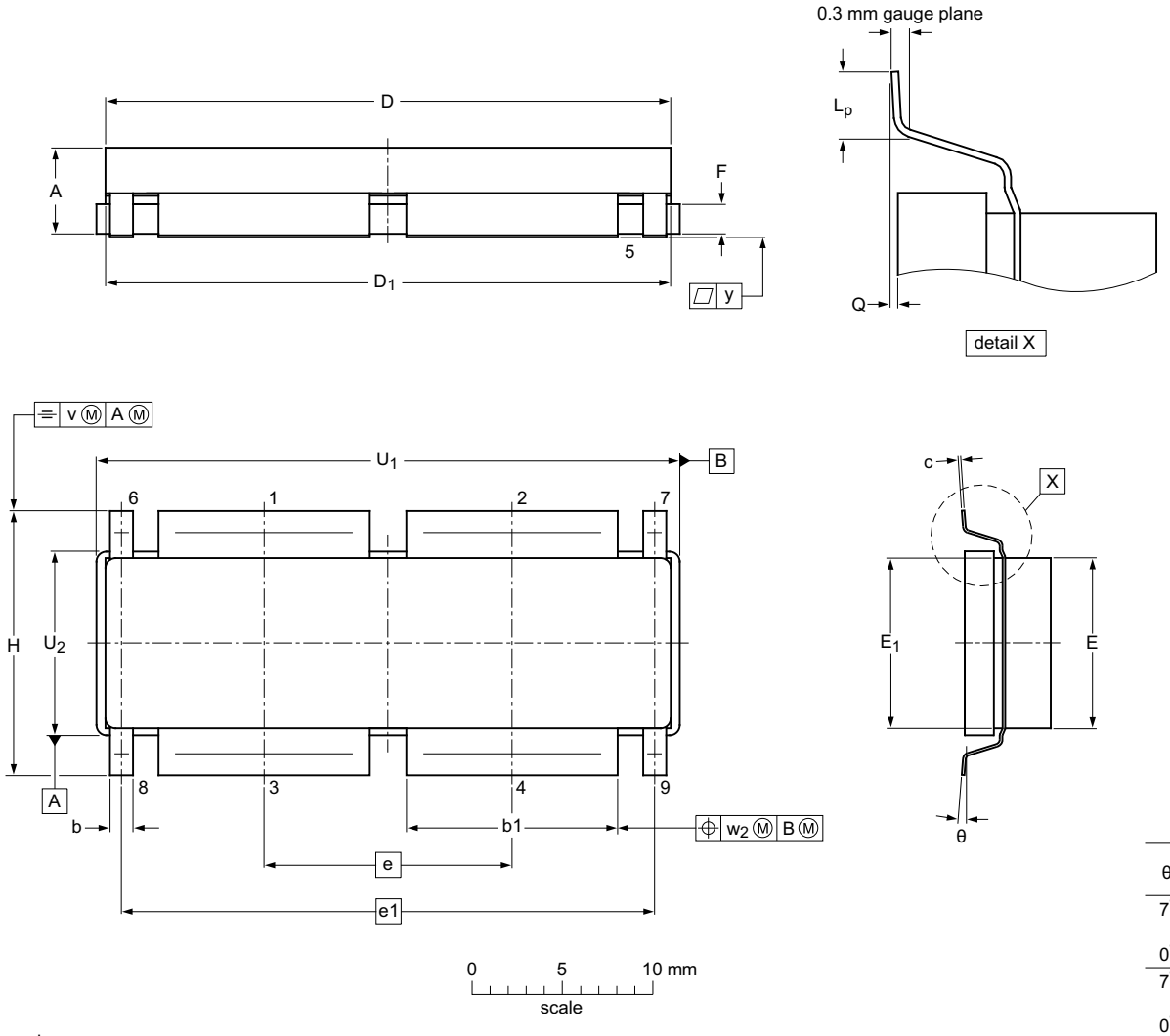
Note
1. Millimeter dimensions are derived from the original inch dimensions.
2. Dimension is measured 0.030 inch (0.76 mm) from the body.

*sot1242b_po*

| Outline version | References | | | | European projection | Issue date |
|---|---|---|---|---|---|---|
| | IEC | JEDEC | JEITA | | | |
| SOT1242B | | | | | | ~~12-05-08~~ 12-11-28 |

**Fig 21. Package outline SOT1242B**

**Earless flanged ceramic package; 8 leads** **SOT1242C**




Dimensions

| Unit[1] | | A | b | b1 | c | D | $D_1$ | e | e1 | E | $E_1$ | F | H | $L_p$ | Q | $U_1$ | $U_2$ | v | $w_2$ | y |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| mm | max | 5.5 | 1.41 | 11.81 | 0.18 | 31.55 | 31.52 | | | 9.50 | 9.53 | 1.75 | 14.70 | 1.38 | 0.195 | 32.39 | 10.29 | 0.25 | 0.25 | 0.15 |
| | nom | | | | | | | 13.72 | 29.47 | | | | | | | | | | | |
| | min | 4.2 | 1.14 | 11.56 | 0.10 | 30.94 | 30.96 | | | 9.30 | 9.27 | 1.50 | 14.50 | 0.98 | 0.045 | 32.13 | 10.03 | | | |
| inches | max | 0.217 | 0.055 | 0.465 | 0.007 | 1.242 | 1.241 | | | 0.374 | 0.375 | 0.069 | 0.579 | 0.055 | 0.008 | 1.275 | 0.405 | 0.01 | 0.01 | 0.006 |
| | nom | | | | | | | 0.540 | 1.16 | | | | | | | | | | | |
| | min | 0.165 | 0.045 | 0.455 | 0.004 | 1.218 | 1.219 | | | 0.366 | 0.365 | 0.059 | 0.571 | 0.039 | 0.002 | 1.265 | 0.395 | | | |

| θ |
|---|
| 7° |
| 0° |
| 7° |
| 0° |

Note
1. Millimeter dimensions are derived from the original inch dimensions.

*sot1242c_po*

| Outline version | References | | | | European projection | Issue date |
|---|---|---|---|---|---|---|
| | IEC | JEDEC | JEITA | | | |
| SOT1242C | | | | | | ~~12-05-15~~ 12-05-30 |

**Fig 22. Package outline SOT1242C**

## 9. Handling information

**CAUTION**

This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

## 10. Abbreviations

**Table 10. Abbreviations**

| Acronym | Description |
|---|---|
| 3GPP | 3rd Generation Partnership Project |
| CCDF | Complementary Cumulative Distribution Function |
| CW | Continuous Wave |
| DPCH | Dedicated Physical Channel |
| ESD | ElectroStatic Discharge |
| IMD | InterModulation Distortion |
| IS-95 | Interim Standard 95 |
| LDMOS | Laterally Diffused Metal Oxide Semiconductor |
| MTF | Median Time to Failure |
| PAR | Peak-to-Average Ratio |
| SMD | Surface Mounted Device |
| VSWR | Voltage Standing Wave Ratio |
| W-CDMA | Wideband Code Division Multiple Access |

## 11. Revision history

**Table 11. Revision history**

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---|---|---|---|---|
| BLF8G20LS-400PV_LS-400PGV v.3 | 20140603 | Product data sheet | - | BLF8G20LS-400PV _LS-400PGV v.2 |
| Modifications | • Section 7.4 on page 6: section updated<br>• Section 7.5 on page 7: section updated | | | |
| BLF8G20LS-400PV_LS-400PGV v.2 | 20130625 | Product data sheet | - | BLF8G20LS-400PV _LS-400PGV v.1 |
| BLF8G20LS-400PV_LS-400PGV v.1 | 20130606 | Preliminary data sheet | - | - |

# 12. Legal information

## 12.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|---|---|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

## 12.2 Definitions

**Draft —** The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

**Short data sheet —** A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification —** The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

## 12.3 Disclaimers

**Limited warranty and liability —** Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

**Right to make changes —** NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use —** NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications —** Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

**Limiting values —** Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

**Terms and conditions of commercial sale —** NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

**No offer to sell or license —** Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control —** This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

**Non-automotive qualified products —** Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

**Translations —** A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

### 12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 13. Contact information

For more information, please visit: **http://www.nxp.com**

For sales office addresses, please send an email to: **salesaddresses@nxp.com**

## 14. Contents





For more information, please visit: http://www.nxp.com
For sales office addresses, please send an email to: salesaddresses@nxp.com

**Date of release: 3 June 2014**
**Document identifier: BLF8G20LS-400PV_LS-400PGV**